

## Diode

Fast switching Emitter Controlled 3 diode chip  
**SIDC03D120H8**

Data Sheet

Industrial Power Control



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## Fast switching Emitter Controlled 3 diode chip

### Features:

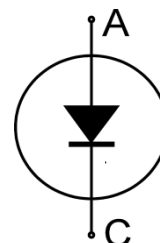
- 1200V Emitter Controlled technology  
120µm chip
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient

### Recommended for:

- Power modules
- Discrete devices

### Applications:

- SMPS
- Resonant applications
- Drives



Chip Type	$V_R$	$I_{Fn}$	Die Size	Package
SIDC03D120H8	1200V	3A	1.75mm x 1.85mm	Sawn on foil

### Mechanical Parameters

Die size	1.75 x 1.85	mm <sup>2</sup>
Area total	3.24	
Anode pad size	See chip drawing	
Silicon thickness	120	µm
Wafer size	200	mm
Maximum possible chips per wafer	8701	
Passivation frontside	Photoimide	
Pad metal	3.2µm AlSiCu	
Backside metal	Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process	
Die bond	Electrically conductive epoxy glue and soft solder	
Wire bond	Al, ≤ 500µm	
Reject ink dot size (valid for inked delivery form only)	Ø 0.65mm; max 1.2mm	
Storage environment (<6 months)	for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C
	for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.

## Maximum Ratings

In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

Not subject to production test, specified by design.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage, $T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
Continuous forward current, limited by $T_{vj\max}^1$	$I_F$	-	A
Maximum repetitive forward current, $t_p$ limited by $T_{vj\max}$	$I_{FRM}$	6	
Virtual junction temperature	$T_{vj}$	-40...+175	$^{\circ}\text{C}$

## Static Characteristics (tested on wafer), $T_{vj}=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	$I_R$	$V_R = 1200\text{V}$	-	-	27.0	$\mu\text{A}$
Cathode-anode breakdown voltage	$V_{BR}$	$I_R = 0.25\text{mA}$	1200	-	-	V
Forward voltage drop	$V_F$	$I_F = 3\text{A}$	1.23	1.6	1.97	

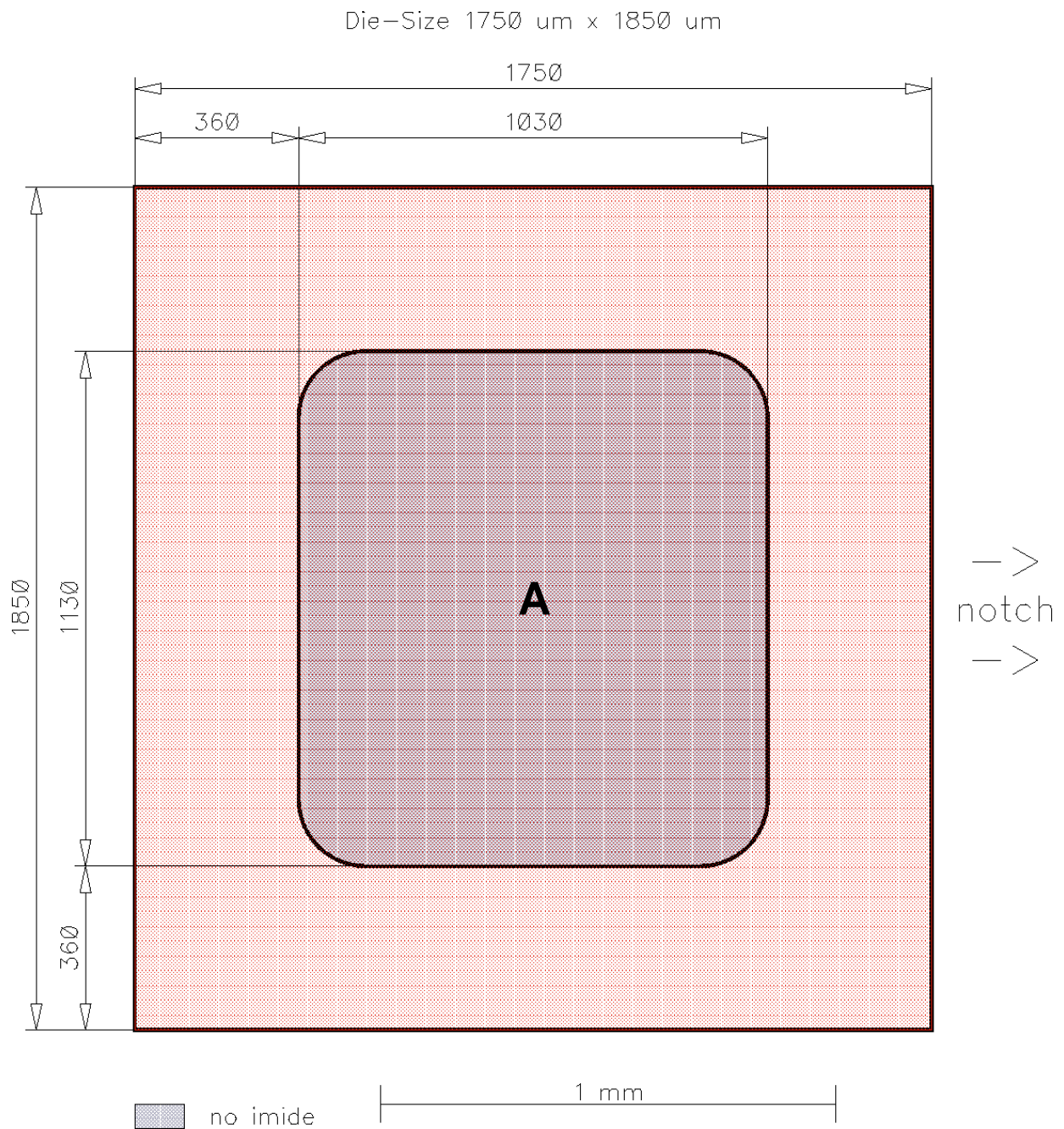
## Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Application example	-	-
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<sup>1</sup> Depending on thermal properties of assembly.

## Chip Drawing



**A** = Anode pad



# SIDC03D120H8

## Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

## Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

## Revision History

Revision	Subjects (major changes since last revision)	Date
2.0	Final data sheet	30.12.2014
2.1	Editorial changes	14.10.2015
2.2	$I_F + I_{FRM}$ conditions changed, $T_{vj}$ increased to 175°C, editorial changes	23.12.2021

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